

UTC UNISONIC TECHNOLOGIES CO., LTD

BAS316 DIODE

HIGH-SPEED DIODE

DESCRIPTION

The UTC BAS316 is high-speed diode, it uses UTC's advanced technology to provide customers with high switching speed, etc.

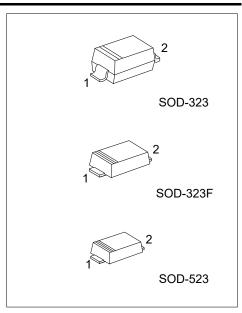
The UTC BAS316 is suitable for high-speed switching in e.g. surface mounted circuits.



* High switching speed

SYMBOL

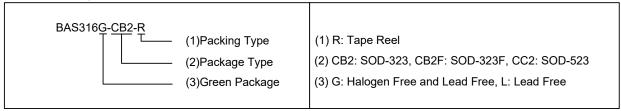




ORDERING INFORMATION

Ordering Number		Dookogo	Pin Ass	Dooking	
Lead Free	Halogen Free	Package	1	2	Packing
BAS316L-CB2-R	BAS316G-CB2-R	SOD-323	K	Α	Tape Reel
BAS316L-CB2F-R	BAS316G-CB2F-R	SOD-323F	K	Α	Tape Reel
BAS316L-CC2-R	BAS316G-CC2-R	SOD-523	К	Α	Tape Reel

Pin Assignment: A: Anode Note: K: Cathode



MARKING



BAS316

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER			SYMBOL	RATINGS	UNIT
repetitive Peak Reverse Voltage			V_{RRM}	85	V
Continuous Reverse Voltage			V_{R}	75	V
Continuous Forward Current T _S =90°C (Note 1)			l _F	250	mA
Repetitive Peak Forward Current			I_{FRM}	500	mA
Non-Repetitive Peak Forward Current	Square Wave,	t=1µs	I _{FSM}	4	Α
		t=1ms		1	Α
		t=1s		0.5	Α
Total Power Dissipation	T _S =90°C (Note 1) (T _A =25°C)		Б	400	mW
			P_D	200	mW
Operating Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-65 ~ +150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	θја	500	°C/W	
Junction to Soldering Point (Note 2)	θ _{JS}	150	°C/W	

Notes: 1. T_S is the temperature at the soldering point of the cathode tab.

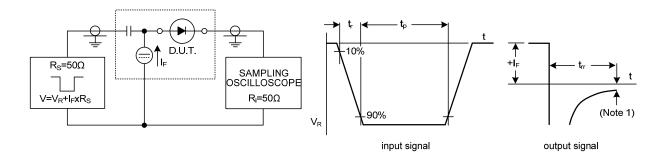
■ ELECTRICAL CHARACTERISTICS (T」=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Forward Voltage	VF	I _F =1mA			715	mV
		I _F =10mA			855	mV
		I _F =50mA			1	V
		I _F =150mA			1.25	V
Reverse Current	I _R	V _R =25V			30	nA
		V _R =75V			1	μΑ
		V _R =25V, T _J =150°C			30	μΑ
		V _R =75V, T _J =150°C			50	μΑ
Diode Capacitance	CD	f=1MHz, V _R =0			1.5	рF
Reverse Recovery Time		When Switched from I _F =10mA to I _R =10mA,				
		R_L =100Ω, Measured at			4	ns
		I _R =1mA, See Fig.1				
Forward Recovery Voltage	\/-	When Switched from I _F =10mA, t _r =20ns, See			1.75	V
		Fig.2			1.73	V

^{2.} Soldering point of the cathode tab.

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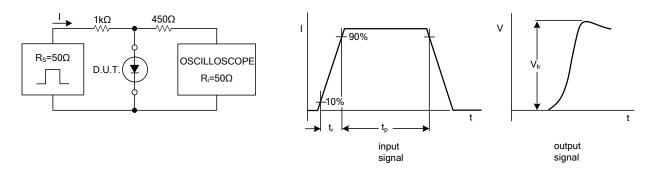
■ TEST CIRCUITS AND WAVEFORMS



Note 1. I_R=1mA.

Input signal: reverse pulse rise time t=0.6ns; reverse voltage pulse duration tp=100ns; duty factor δ =0.05; Oscilloscope: rise time t=0.35ns.

Fig.1 Reverse Recovery Voltage Test Circuit and Waveforms.



Input signal: forward pulse rise time t_r =20ns; forward current pulse duration t_p ≥100ns; duty factor δ ≤ 0.005.

Fig.2 Forward Recovery Voltage Test Circuit and Waveforms.

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